

DESCRIPTION

The HYM532200A is a 2M x 32-bit Fast page mode CMOS DRAM module consisting of sixteen HY514400A in 20/26 pin SOJ on a 72 pin glass-epoxy printed circuit board. 0.22 μ F decoupling capacitor is mounted for each DRAM. The HYM532200AM/ALM are Tin-Lead plated and HYM532200AMG/ALMG are Gold plated socket type Single In-line Memory Modules suitable for easy interchange and addition of 8M byte memory.

FEATURES

Low power dissipation

Max. battery back-up 35.2mW (L-part)

Max. CMOS standby 17.6mW (L-part)
88.0mW

Max. TTL standby 176.0mW

Max. operating

Speed	Power
50	5.81W
60	5.15W
70	4.49W

- Single power supply of 5V $\pm$ 10%
- TTL compatible inputs and outputs
- Fast access time

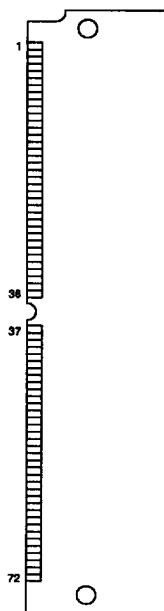
Speed	tRAC	tCAC	tPC
50	50ns	15ns	35ns
60	60ns	15ns	40ns
70	70ns	20ns	45ns

- Fast page mode operation
- CAS-before-RAS, RAS-only, Hidden refresh
- 1024 refresh cycles / 128ms (L-part)
1024 refresh cycles / 16ms

PIN DESCRIPTION

RAS0-RAS3	Row Address Strobe
CAS0-CAS3	Column Address Strobe
WE	Write Enable
A0-A9	Address Input
DQ0-DQ31	Data Input/Output
PD1-PD4	Presence Detect
Vcc	Power (+ 5V)
Vss	Ground

PIN CONNECTION



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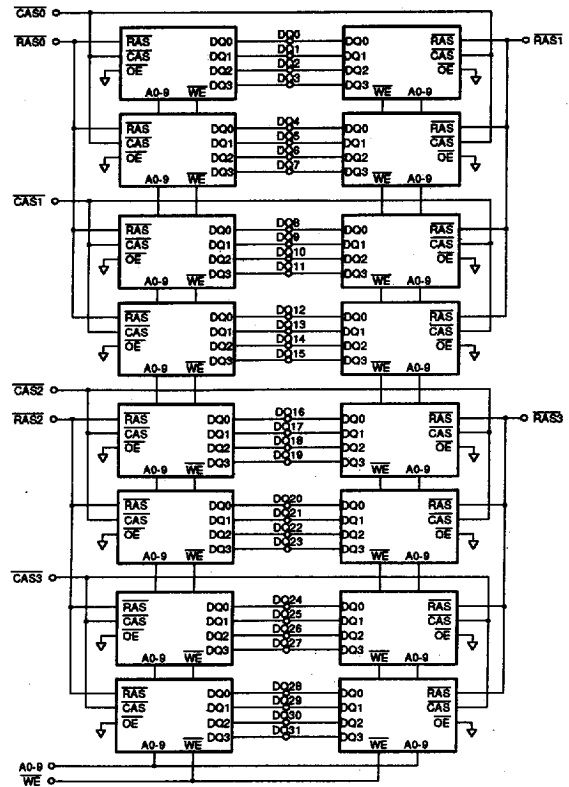
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187

PIN NAME

#	NAME	#	NAME
1	Vss	37	NC
2	DQ0	38	NC
3	DQ16	39	Vss
4	DQ1	40	CAS0
5	DQ17	41	CAS2
6	DQ2	42	CAS3
7	DQ18	43	CAS1
8	DQ3	44	RAS0
9	DQ19	45	RAS1
10	Vcc	46	NC
11	NC	47	WE
12	A0	48	NC
13	A1	49	DQ8
14	A2	50	DQ24
15	A3	51	DQ9
16	A4	52	DQ25
17	A5	53	DQ10
18	A6	54	DQ26
19	NC	55	DQ11
20	DQ4	56	DQ27
21	DQ20	57	DQ12
22	DQ5	58	DQ28
23	DQ21	59	Vcc
24	DQ6	60	DQ29
25	DQ22	61	DQ13
26	DQ7	62	DQ30
27	DQ23	63	DQ14
28	A7	64	DQ31
29	NC	65	DQ15
30	Vcc	66	NC
31	A8	67	PD1
32	A9	68	PD2
33	RAS3	69	PD3
34	RAS2	70	PD4
35	NC	71	NC
36	NC	72	Vss

BLOCK DIAGRAM



PRESENCE DETECT PINS

PIN	-50	-60	-70
PD1	NC	NC	NC
PD2	NC	NC	NC
PD3	Vss	NC	Vss
PD4	Vss	NC	NC

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ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
TA	Ambient Temperature	0 to 70	°C
TSTG	Storage Temperature	-65 to 150	°C
VIN, VOUT	Voltage on Any Pin Relative to Vss	-1.0 to 7.0	V
VCC	Voltage on Vcc Relative to Vss	-1.0 to 7.0	V
Ios	Short Circuit Output Current	50	mA
Pd	Power Dissipation	14.4	W

NOTE : Operation at or above Absolute Maximum Ratings can adversely affect device reliability.

RECOMMENDED DC OPERATING CONDITIONS

(TA= 0°C to 70°C)

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
VCC	Supply Voltage	4.5	5.0	5.5	V
VIH	Input High Voltage	2.4	-	VCC+ 1.0	V
VIL	Input Low Voltage	-1.0	-	0.8	V

NOTE : All voltages are referenced to Vss.

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DC CHARACTERISTICS

(TA= 0°C to 70°C, VCC= 5V± 10%, VSS= 0V, unless otherwise noted.)

SYMBOL	PARAMETER	TEST CONDITIONS	SPEED/ POWER	MIN.	MAX.	UNIT	NOTE
ILI	Input Leakage Current (Any Input Pin)	VSS ≤ VIN ≤ VCC+ 1.0, All other pins not under test= VSS		-160	160	μA	
ILO	Output Leakage Current (High Impedance State)	VSS ≤ VOUT ≤ VCC, RAS & CAS at VIH		-20	20	μA	
Icc1	VCC Supply Current, Operating	tRC= tRC (min.)	50 60 70	- - -	1056 936 816	mA	1,2,3
Icc2	VCC Supply Current, TTL Standby	RAS & CAS at VIH, other inputs ≥ VSS		-	32	mA	
Icc3	VCC Supply Current, RAS-only refresh	tRC= tRC (min.)	50 60 70	- - -	1056 936 816	mA	1,3
Icc4	VCC Supply Current, Fast Page mode	tPC= tPC (min.)	50 60 70	- - -	656 576 496	mA	1,2,3
Icc5	VCC Supply Current, CMOS Standby	RAS & CAS ≥ VCC-0.2V	L-part	- -	16 3.2	mA	5
Icc6	VCC Supply Current, CAS-before-RAS refresh	tRC= tRC (min.)	50 60 70	- - -	1056 936 816	mA	1,3
Icc7	VCC Supply Current, Battery Back Up (L-part only)	tRC= 125μs, CAS= CBR cycling or 0.2V WE= VCC-0.2V A0-A9= VCC-0.2V or 0.2V DQ0-DQ31= VCC-0.2V, 0.2V, or open	tRAS ≤ 300ns	-	0.6	mA	1,4,5
			tRAS ≤ 1μs	-	1		
VOL	Output Low Voltage	IOL= 4.2mA		-	0.4	V	
VOH	Output High Voltage	IOH= -5mA		2.4	-	V	

NOTE :

1. Icc1, Icc3, Icc4, Icc6 and Icc7 depend on cycle rate.
2. Icc1 and Icc4 depend on output loading. Specified values are obtained with the output open.
3. It depends on user whether column address is changed or not at least once while RAS= VIL and CAS= VIH.
4. Only tRAS(max.)= 1μs is applied to refresh of battery backup but tRAS(max.)= 10μs is applied to normal functional operation.
5. Icc5(max.)= 3.2mA and Icc7 are applied to L-part only (HYM532200ALM and HYM532200ALMG).

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AC CHARACTERISTICS

(TA= 0°C to 70°C, VCC= 5V± 10%, VSS= 0V, unless otherwise noted.) NOTE : 1, 2, 3

HYM532200AM/ALM/AMG/ALMG

#	SYMBOL	PARAMETER	HYM532200AM/ALM/AMG/ALMG						UNIT	NOTE
			-50		-60		-70			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
1	tRC	Random Read or Write Cycle Time	90	-	110	-	130	-	ns	
2	tRPC	RAS to CAS Precharge Time	0	-	0	-	0	-	ns	
3	tPC	Fast Page Mode Cycle Time	35	-	40	-	45	-	ns	
4	tRHCP	RAS Hold Time from CAS Precharge	30	-	35	-	40	-	ns	
5	tRAC	Access Time from RAS	-	50	-	60	-	70	ns	4,9,10
6	tCAC	Access Time from CAS	-	15	-	15	-	20	ns	4,9
7	tAA	Access Time from Column Address	-	25	-	30	-	35	ns	4,10
8	tCPA	Access Time from CAS Precharge	-	30	-	35	-	40	ns	4
9	tCLZ	CAS to Output Low Impedance	0	-	0	-	0	-	ns	4
10	tOFF	Output Buffer Turn-off Delay	0	15	0	15	0	20	ns	5
11	tT	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	3
12	tRP	RAS Precharge Time	30	-	40	-	50	-	ns	
13	tRAS	RAS Pulse Width	50	10K	60	10K	70	10K	ns	
14	tRASP	RAS Pulse Width (Fast Page Mode)	50	200K	60	200K	70	200K	ns	
15	tRSH	RAS Hold Time	15	-	15	-	20	-	ns	
16	tCSH	CAS Hold Time	50	-	60	-	70	-	ns	
17	tCAS	CAS Pulse Width	15	10K	15	10K	20	10K	ns	
18	tRCD	RAS to CAS Delay	15	35	20	45	20	50	ns	9
19	tRAD	RAS to Column Address Delay Time	10	25	15	30	15	35	ns	10
20	tCRP	CAS to RAS Precharge Time	5	-	5	-	5	-	ns	
21	tCP	CAS Precharge Time	10	-	10	-	10	-	ns	
22	tASR	Row Address Set-up Time	0	-	0	-	0	-	ns	
23	tRAH	Row Address Hold Time	5	-	10	-	10	-	ns	
24	tASC	Column Address Set-up Time	0	-	0	-	0	-	ns	
25	tCAH	Column Address Hold Time	15	-	15	-	15	-	ns	
26	tAR	Column Address Hold Time from RAS	45	-	50	-	55	-	ns	
27	tRAL	Column Address to RAS Lead Time	25	-	30	-	35	-	ns	
28	tRCS	Read Command Set-up Time	0	-	0	-	0	-	ns	
29	tRCH	Read Command Hold Time Referenced to CAS	0	-	0	-	0	-	ns	6
30	tRRH	Read Command Hold Time Referenced to RAS	0	-	0	-	0	-	ns	6
31	tWCH	Write Command Hold Time	10	-	15	-	15	-	ns	
32	tWCR	Write Command Hold Time from RAS	40	-	50	-	55	-	ns	
33	tWP	Write Command Pulse Width	10	-	15	-	15	-	ns	
34	tRWL	Write Command to RAS Lead Time	15	-	15	-	20	-	ns	
35	tCWL	Write Command to CAS Lead Time	15	-	15	-	20	-	ns	
36	tDS	Data-In Set-up Time	0	-	0	-	0	-	ns	7
37	tDH	Data-In Hold Time	10	-	15	-	15	-	ns	7
38	tDHR	Data-In Hold Time Referenced to RAS	40	-	50	-	55	-	ns	
39	tREF	Refresh Period (1024 cycles)	-	16	-	16	-	16	ms	
		L-part	-	128	-	128	-	128		11
40	tWCS	Write Command Set-up Time	0	-	0	-	0	-	ns	8

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AC CHARACTERISTICS

(continued)

(continued)

#	SYMBOL	PARAMETER	HYM532200AM/ALM/AMG/ALMG						UNIT	NOTE
			-50		-60		-70			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
41	tCSR	CAS Set-up Time (CBR Cycle)	5	-	5	-	5	-	ns	
42	tCHR	CAS Hold Time (CBR Cycle)	10	-	10	-	10	-	ns	
43	tCPT	CAS Precharge Time (CBR Counter Test)	25	-	30	-	35	-	ns	
44	tWRP	WE to RAS Precharge Time (CBR Cycle)	10	-	10	-	10	-	ns	
45	tWRH	WE to RAS Hold Time (CBR Cycle)	10	-	10	-	10	-	ns	

4675088 0005551 164

NOTE :

1. An initial pause of 200 μ s is required after power-up followed by 8 RAS cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS-before-RAS initialization cycles instead of 8 RAS-only refresh cycles are required. The device should be carefully initialized to be prevented from being entered into multi bit test mode.
2. VIH(min.) and VIL(max.) are reference levels for measuring timing of input signals. Transition time is measured between VIH and VIL and assumed to be 5ns for all inputs.
3. Refer to the HY514400A data sheet for detailed information.
4. Measured with a load equivalent to 2 TTL loads and 100pF.
5. tOFF(max.) defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
6. Either tRCH or tRRH must be satisfied for a read cycle.
7. These parameters are referenced to CAS leading edge in early write cycles.
8. twCS is not a restrictive operating parameter. It is included in the data sheet as electrical characteristics only. If twCS $\geq$ twCS(min.), the cycle is an early write cycle and data out pin will remain open circuit (high impedance) through the entire cycle.
9. Operation within the tRCD(max.) limit insures that tRAC(max.) can be met. tRCD(max.) is specified as a reference point only. If tRCD is greater than the specified tRCD(max.) limit, then access time is controlled by tCAC.
10. Operation within the tRAD(max.) limit insures that tRAC(max.) can be met. tRAD(max.) is specified as a reference point only. If tRAD is greater than the specified tRAD(max.) limit, then access time is controlled by tAA.
11. tREF(max.) = 128ms is applied to L-part only (HYM532200ALM and HYM532200ALMG).

CAPACITANCE

(TA = 25°C, VCC = 5V $\pm$ 10%, VSS = 0V, f = 1MHz, unless otherwise noted.)

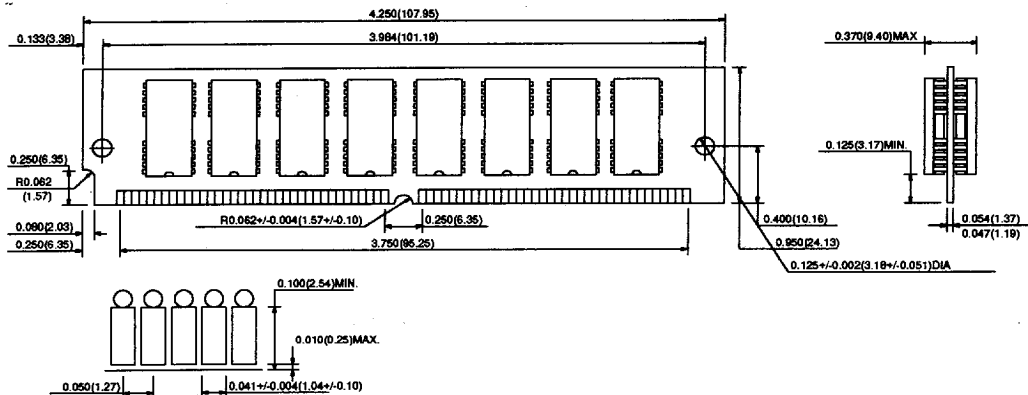
SYMBOL	PARAMETER	TYP.	MAX.	UNIT
CIN1	Input Capacitance (A0-A9)	-	125	pF
CIN2	Input Capacitance (WE)	-	140	pF
CIN3	Input Capacitance (RAS0-RAS3)	-	40	pF
CIN4	Input Capacitance (CAS0-CAS3)	-	40	pF
CDQ	Data Input/Output Capacitance (DQ0-DQ31)	-	28	pF

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PACKAGE INFORMATION

72 pin Single In-line Memory Module (M ; Tin-Lead plated, MG ; Gold plated)

UNIT : INCH(mm)
TOLERANCE : +/-0.005(0.13)



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ORDERING INFORMATION

PART NUMBER	SPEED	POWER	PACKAGE	PLATING
HYM532200AM	50/60/70		SIMM	Tin-Lead
HYM532200ALM	50/60/70	L-part	SIMM	Tin-Lead
HYM532200AMG	50/60/70		SIMM	Gold
HYM532200ALMG	50/60/70	L-part	SIMM	Gold

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